Po-Hsun Ho

List of Publications by Year in descending order

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15	717	840776 11	996975 15 g-index
papers	citations	h-index	g-maex
15 all docs	15 docs citations	15 times ranked	1676 citing authors

#	Article	IF	CITATIONS
1	Fast growth of large-grain and continuous MoS2 films through a self-capping vapor-liquid-solid method. Nature Communications, 2020, 11, 3682.	12.8	76
2	High-Mobility InSe Transistors: The Nature of Charge Transport. ACS Applied Materials & Samp; Interfaces, 2019, 11, 35969-35976.	8.0	23
3	Spatially and Precisely Controlled Large-Scale and Persistent Optical Gating in a TiOx–MoS2 Heterostructure. ACS Applied Materials & Interfaces, 2018, 10, 38319-38325.	8.0	2
4	Environment-insensitive and gate-controllable photocurrent enabled by bandgap engineering of MoS2 junctions. Scientific Reports, 2017, 7, 44768.	3.3	11
5	Surface Oxidation Doping to Enhance Photogenerated Carrier Separation Efficiency for Ultrahigh Gain Indium Selenide Photodetector. ACS Photonics, 2017, 4, 2930-2936.	6.6	44
6	High-Mobility InSe Transistors: The Role of Surface Oxides. ACS Nano, 2017, 11, 7362-7370.	14.6	177
7	Observation of quantum Hall plateau-plateau transition and scaling behavior of the zeroth Landau level in graphene <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>p</mml:mi><mml:mtext>â^'<td>nl:m³text><</td><td>m‰l:mi>n<</td></mml:mtext></mml:mrow></mml:math>	nl:m³text><	m‰l:mi>n<
8	Precisely Controlled Ultrastrong Photoinduced Doping at Graphene–Heterostructures Assisted by Trapâ€Stateâ€Mediated Charge Transfer. Advanced Materials, 2015, 27, 7809-7815.	21.0	39
9	Sunlight-activated graphene-heterostructure transparent cathodes: enabling high-performance n-graphene/p-Si Schottky junction photovoltaics. Energy and Environmental Science, 2015, 8, 2085-2092.	30.8	42
10	Selfâ€Crackâ€Filled Graphene Films by Metallic Nanoparticles for Highâ€Performance Graphene Heterojunction Solar Cells. Advanced Materials, 2015, 27, 1724-1729.	21.0	65
11	Extrinsic Origin of Persistent Photoconductivity in Monolayer MoS2 Field Effect Transistors. Scientific Reports, 2015, 5, 11472.	3.3	110
12	Wavelengthâ€Selective Dual p―and nâ€Type Carrier Transport of an Organic/Graphene/Inorganic Heterostructure. Advanced Materials, 2015, 27, 282-287.	21.0	26
13	Residue-free fabrication of high-performance graphene devices by patterned PMMA stencil mask. AIP Advances, 2014, 4, .	1.3	11
14	Dependence of Nanocrystal Dimensionality on the Polymer Nanomorphology, Anisotropic Optical Absorption, and Carrier Transport in P3HT:TiO ₂ Bulk Heterojunctions. Journal of Physical Chemistry C, 2012, 116, 25081-25088.	3.1	10
15	Self-Encapsulated Doping of n-Type Graphene Transistors with Extended Air Stability. ACS Nano, 2012, 6, 6215-6221.	14.6	76